

**PATENT APPLICATION**

Sheet 1 of 6

<b>FORM PTO-1449</b>  <b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)	<b>ATTY. DOCKET NO.</b> <b>200315719-1</b>	<b>APPLICATION NO.</b> <b>10/799, 318</b>	<b>CONFIRMATION NO.</b>
	<b>APPLICANT</b> <b>Randy L. Hoffman, et al.</b>		
	<b>FILING DATE</b> <b>Herewith</b>	<b>GROUP</b>	

**REFERENCE DESIGNATION U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
/M.P./	1A	4,887,255	12/12/1989	Handa, et al.	
	1B	5,744,864	04/28/1998	Cillessen, et al.	
	1C	6,225,655	05/01/2001	Moise, et al.	
	1D	6,255,130	07/03/2001	Kim	
	1E	6,362,499	03/26/2002	Moise, et al.	
	1F	6,563,174	05/13/2003	Kawasaki, et al.	
	1G	2003/0013261	01/16/2003	Asano	
	1H	2002/0153587	10/24/2002	Adkisson, et al.	
	1I	2003/0207502	11/06/2003	Yamazaki, et al.	
	1J	2003/0218221	11/27/2003	Wager, III, et al.	
/M.P./	1K	2003/0218222	11/27/2003	Wager, III, et al.	

**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
/M.P./	1L	WO 97/06544	02/20/1997	Cillessen, et al.		
/M.P./	1M	EP1134811	09/19/2001	Kawasaki, et al.		
	1N					
	1O					
	1P					

**OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)**

/M.P./	1Q	Aoki, Akira, et al., "Tin Oxide Thin Film Transistors", Japan J. Appl. Phys., Vol. 9, p.582 (1970).
/M.P./	1R	Carcia, P.F., et al., "Transparent ZnO thin-film transistor fabricated by rf magnetron sputtering", Applied Physics Letters, Vol. 82, No. 7, pp. 1117-1119 (February 17, 2003).
/M.P./	1S	Carcia, P.F., et al., "ZnO Thin Film Transistors for Flexible Electronics", Mat. Res. Soc. Symp. Proc., Vol. 769, pp. H72.1-H72.6 (2003).

EXAMINER

DATE CONSIDERED

FORM PTO-1449  LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)	ATTY. DOCKET NO. <b>200315719-1</b>	APPLICATION NO. <b>10/799,318</b>	CONFIRMATION NO.
	APPLICANT <b>Randy L. Hoffman, et al.</b>		
	FILING DATE <b>Herewith</b>	GROUP	

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
/M.P./	2A	2003/0219530	11/27/2003	Yamazaki, et al.	
	2B	2003/0111663	06/19/2003	Yagi	
	2C	2003/0047785	03/13/2003	Kawasaki, et al.	
	2D	60/490,239	07/25/2003		Transparent Thin Film Transistor with Zinc-Tin Oxide Channel...
	2E	10/763,353	01/23/2004		Semiconductor Device
/M.P./	2F	10/763,354	01/23/2004		Transistor including a Deposited Channel Region Having a ...
	2G				
	2H				
	2I				
	2J				
	2K				

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	2L					
	2M					
	2N					
	2O					
	2P					

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

/M.P./	2Q	Fu, Shelton, et al., "MOS and MOSFET with Transistion Metal Oxides", SPIE Vol. 2697, pp. 520-527. unknown date
/M.P./	2R	Giesbers, J.B., et al., "Dry Etching of All-Oxide Transparent Thin Film Memory Transistors", Microeletronic Engineering, Vol. 35, pp. 71-74 (1997).
/M.P./	2S	Grosse-Holz, K.O., et al. "Semiconductive Behavior of Sb Doped SnO2 Thin Films", Mat. Res. Soc. Symp. Proc., Vol. 401, pp. 67-72 (1996).

EXAMINER	DATE CONSIDERED
----------	-----------------

FORM PTO-1449	ATTY. DOCKET NO. <b>200315719-1</b>	APPLICATION NO. <b>10/799,318</b>	CONFIRMATION NO.
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	APPLICANT <b>Randy L. Hoffman, et al.</b>		
	FILING DATE	GROUP	
	Herewith		
(Use several sheets if necessary)			

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	3A			
	3B			
	3C			
	3D			
	3E			
	3F			
	3G			
	3H			
	3I			
	3J			
	3K			

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	3L				
	3M				
	3N				
	3O				
	3P				

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

/M.P./	3Q	Hoffman, R.L., et al., "ZnO-based transparent thin-film transistors", Applied Physics Letters, Vol. 82, No. 5, pp. 733-735 (February 3, 2003).
/M.P./	3R	Masuda, Satoshi, et al., "Transparent thin film transistors using ZnO as an active channel layer and their electrical properties", Journal of Applied Physics, Vol. 93, No. 3, pp. 1624-1630 (February 1, 2003).
/M.P./	3S	Nishi, Junya, et al., "High Mobility Thin Film Transistors with Transparent ZnO Channels", Jpn. J. Appl. Phys., Vol. 42, Part 2, No. 4A, pp. L347-L349 (April, 2003).

EXAMINER	DATE CONSIDERED
----------	-----------------

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR  
APPLICANT'S INFORMATION DISCLOSURE  
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200315719-1

APPLICATION NO.

10/799, 318

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

FILING DATE

Herewith

GROUP

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	4A			
	4B			
	4C			
	4D			
	4E			
	4F			
	4G			
	4H			
	4I			
	4J			
	4K			

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	4L				
	4M				
	4N				
	4O				
	4P				

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

/M.P./	4Q	Ohya, Yutaka, et al., "Thin Film Transistor of ZnO Fabricated by Chemical Solution Deposition", Jpn. J. Appl. Phys., Vol. 40, Part 1, No. 1, pp. 297-298 (January, 2001).
/M.P./	4R	Pallecchi, Ilaria, et al., "SrTiO <sub>3</sub> -based metal-insulator-semiconductor heterostructures" Applied Physics Letters, Vol. 78, No. 15, pp. 2244-2246 (April 9, 2001).
/M.P./	4S	Prins, M. W. J., et al., "A ferroelectric transparent thin-film transistor", Appl. Phys. Lett., Vol. 68, No. 25, pp. 3650-3652 (June 17, 1996).

EXAMINER

DATE CONSIDERED

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR  
APPLICANT'S INFORMATION DISCLOSURE  
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200315719-1

APPLICATION NO.

10/799,318

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

FILING DATE

GROUP

Herewith

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	5A			
	5B			
	5C			
	5D			
	5E			
	5F			
	5G			
	5H			
	5I			
	5J			
	5K			

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	5L				
	5M				
	5N				
	5O				
	5P				

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

/M.P./	5Q	Seager, C.H., et al., "Charge Trapping and device behavior in ferroelectric memories", Appl. Phys. Lett., Vol. 68, No. 19, pp. 2660-2662 (May 6, 1996).
/M.P./	5R	Uneno, K., et al. "Field-effect transistor on SrTiO <sub>3</sub> with sputtered Al <sub>2</sub> O <sub>3</sub> gate insulator", Applied Physics Letters, Vol. 83, No. 9, pp. 1755-1757 (September 1, 2003).
/M.P./	5S	Wöllenstein, Jürgen, et al., "An insulated gate thin-film transistor using SnO <sub>2</sub> as semiconducting channel, a possible new gas sensor device" The 11th European Conference on Solid State Transducers, pp. 471-474 (September 21-24, 1997).

EXAMINER

DATE CONSIDERED

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR  
APPLICANT'S INFORMATION DISCLOSURE  
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

200315719-1

APPLICATION NO.

10/799,318

CONFIRMATION NO.

APPLICANT

Randy L. Hoffman, et al.

FILING DATE

GROUP

Herewith

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	6A			
	6B			
	6C			
	6D			
	6E			
	6F			
	6G			
	6H			
	6I			
	6J			
	6K			

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	6L				
	6M				
	6N				
	6O				
	6P				

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

/M.P./	6Q	Yoshida, A., "Three Terminal Field Effect Superconducting Device Using SrTiO <sub>3</sub> Channel" IEEE Transactions on Applied Superconductivity, Vol. 5, No. 2, pp. 2892-2895 (June, 1995).
/M.P./	6R	Solid-State Electronics, Vol. 7, Pergamon Press, Notes pp. 701-702 (1964).
/M.P./	6S	Anonymous, "Transparent and/or memory thin film transistors in LCD's and PLED_" Research Disclosure, p. 890 (July 1998).

EXAMINER

/Marcos Pizarro Crespo/

DATE CONSIDERED

08/10/2007